

N-Ch 30V Fast Switching MOSFET
 $V_{DS}=30V$, $I_D=4.0A$, $R_{DS(ON)}=42m\Omega$

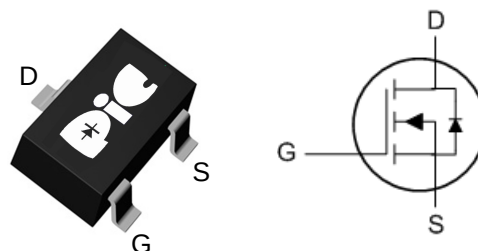
➤ General Description

This PAN3400SN N-Channel enhancement mode power field effect transistor is the high density trench technology and this advanced technology can provide excellent $R_{DS(ON)}$ performance and efficiency for power switching and load switching application., this device also comply with the RoHS and Green Product requirement with full function reliability approved.

➤ Feature

- Super high density cell design for extremely low $R_{DS(ON)}$
- SOT-23 package design

➤ SOT-23



➤ Application

- Power Management in Note book
- LED Display
- DC-DC System
- LCD Panel

➤ Absolute Maximum Ratings

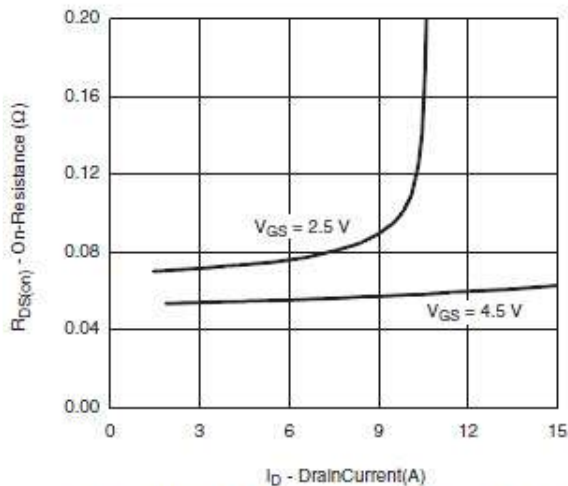
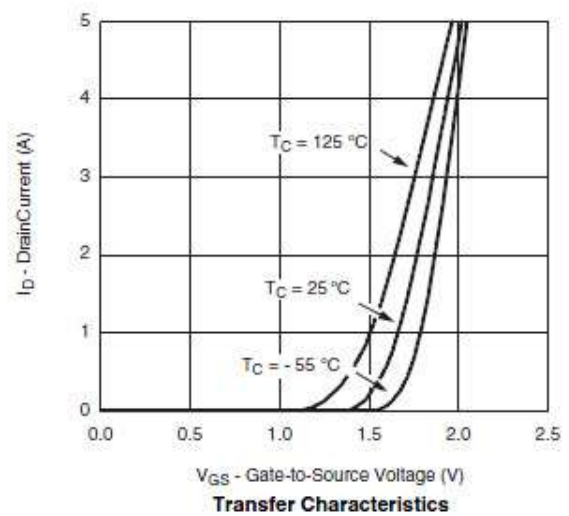
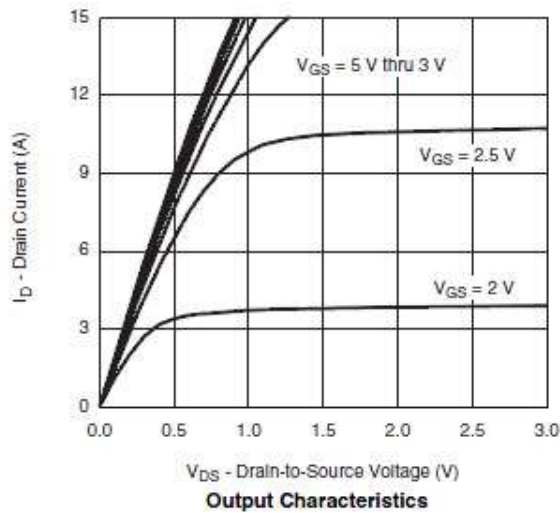
Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	30	V
Gate –Source Voltage	V_{GSS}	± 16	V
Continuous Drain Current($T_J=150^{\circ}C$)	I_D	$T_A=25^{\circ}C$ 4.0	A
		$T_A=70^{\circ}C$ 3.0	
Pulsed Drain Current	I_{DM}	15	A
Continuous Source Current(Diode Conduction)	I_S	1.7	A
Power Dissipation	P_D	$T_A=25^{\circ}C$ 2.0	W
		$T_A=70^{\circ}C$ 1.3	
Operating Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature Range	T_{STG}	-55/150	$^{\circ}C$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	120	$^{\circ}C/W$

➤ **Electrical Characteristics ($T_A=25^\circ C$ Unless otherwise noted)**

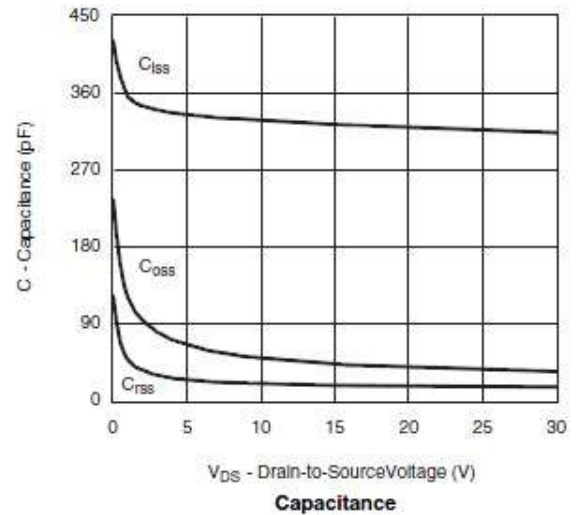
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	30			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.6		1.1	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 16V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=24V, V_{GS}=0V$			1	uA
		$V_{DS}=24V, V_{GS}=0V$ $T_J=85^\circ C$			30	
On-State Drain Current	$I_{D(on)}$	$V_{DS} \geq 5V, V_{GS}=4.5V$	30			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=2.8A$		26	42	mΩ
		$V_{GS}=4.5V, I_D=2.5A$		28	44	
		$V_{GS}=2.5V, I_D=2.2A$		34	50	
Forward Transconductance	g_{FS}	$V_{DS}=10V, I_D=6.1A$		20		S
Diode Forward Voltage	V_{SD}	$I_S=1.7A, V_{GS}=0V$		0.8	1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=15V, V_{GS}=10V$ $I_D=2.6A$		3.0	4.5	nC
Gate-Source Charge	Q_{gs}			1.6		
Gate-Drain Charge	Q_{gd}			0.6		
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V$ $f=1MHz$		320		pF
Output Capacitance	C_{oss}			70		
Reverse Transfer Capacitance	C_{rss}			30		
Turn-On Time	$t_{d(on)}$	$V_{DD}=15V, R_L=15\Omega$ $I_D=1.0A, V_{GEN}=10V$ $R_G=6\Omega$		8	12	ns
	t_r			12	18	
Turn-Off Time	$t_{d(off)}$			15	30	
	t_f			8	15	

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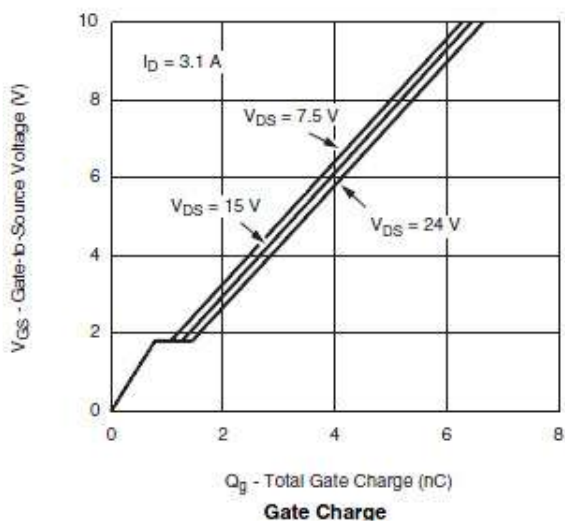
➤ Typical Characteristics



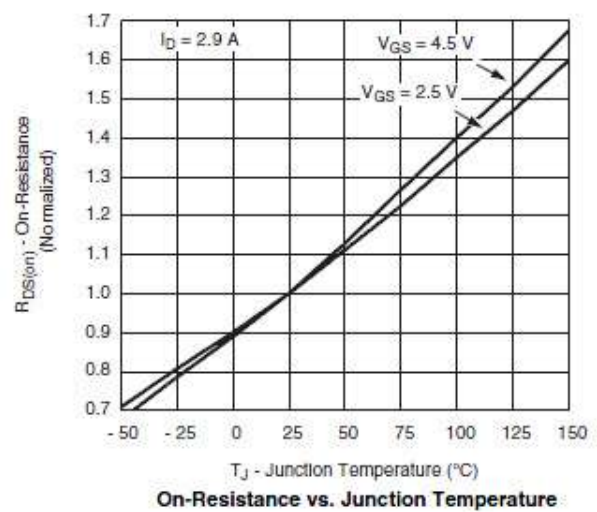
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

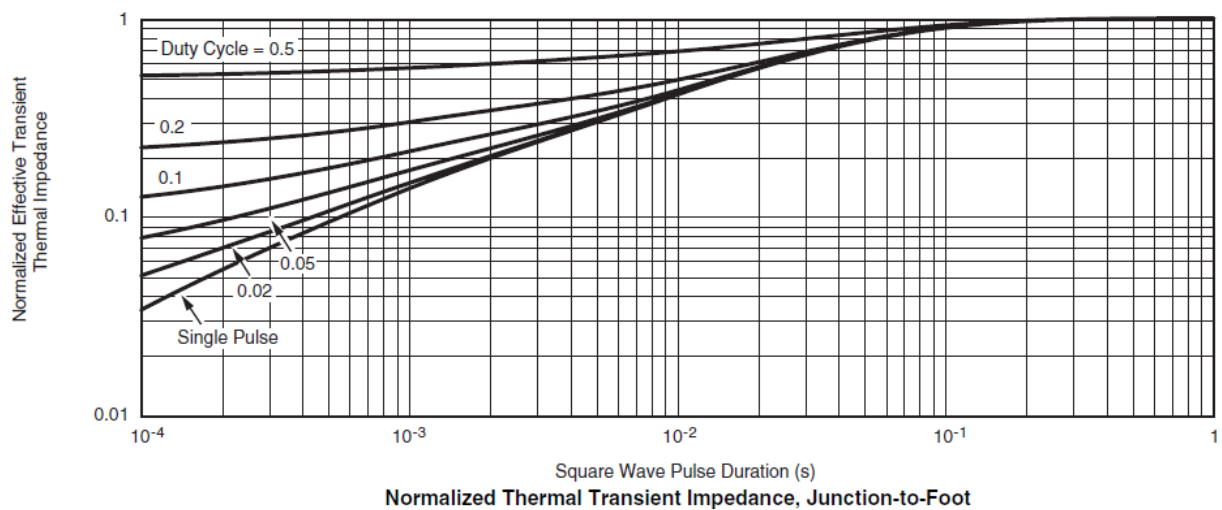
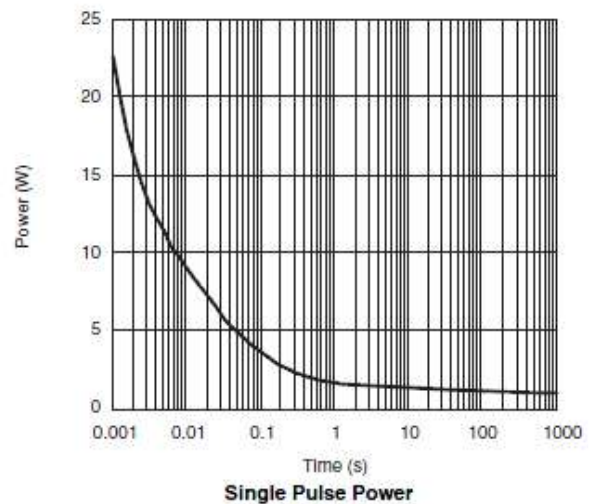
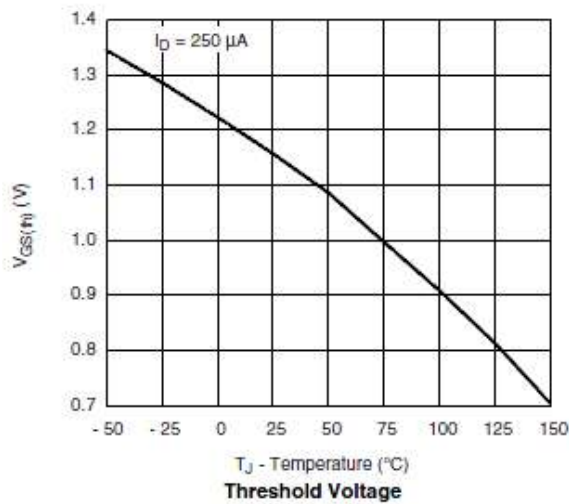
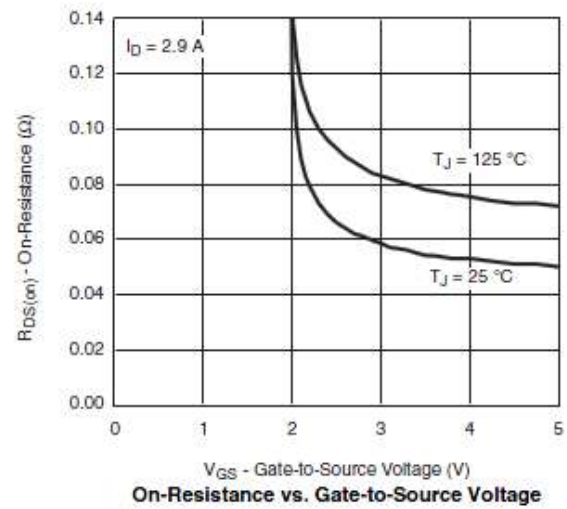
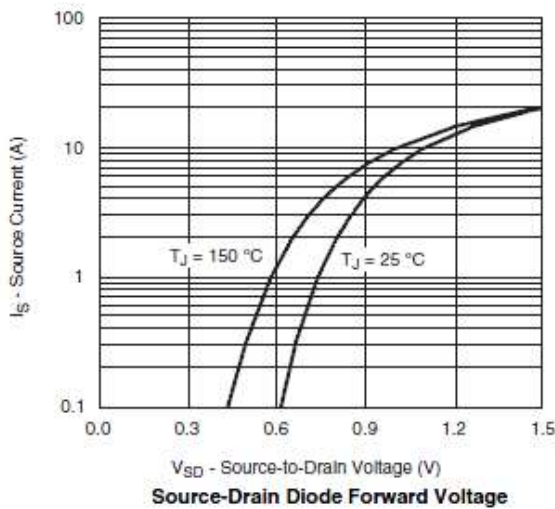


Gate Charge

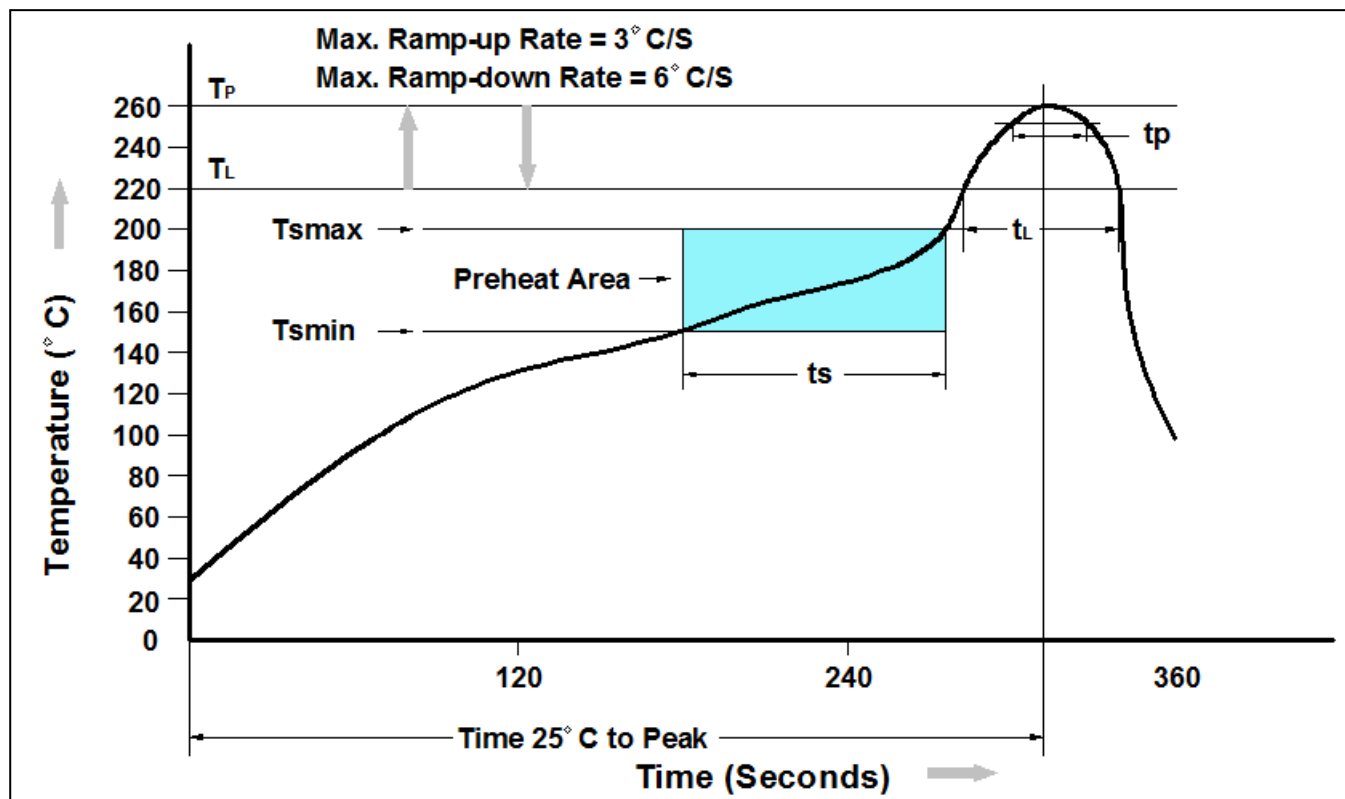


On-Resistance vs. Junction Temperature

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➤ Recommend IR Reflow Soldering Thermal Profile



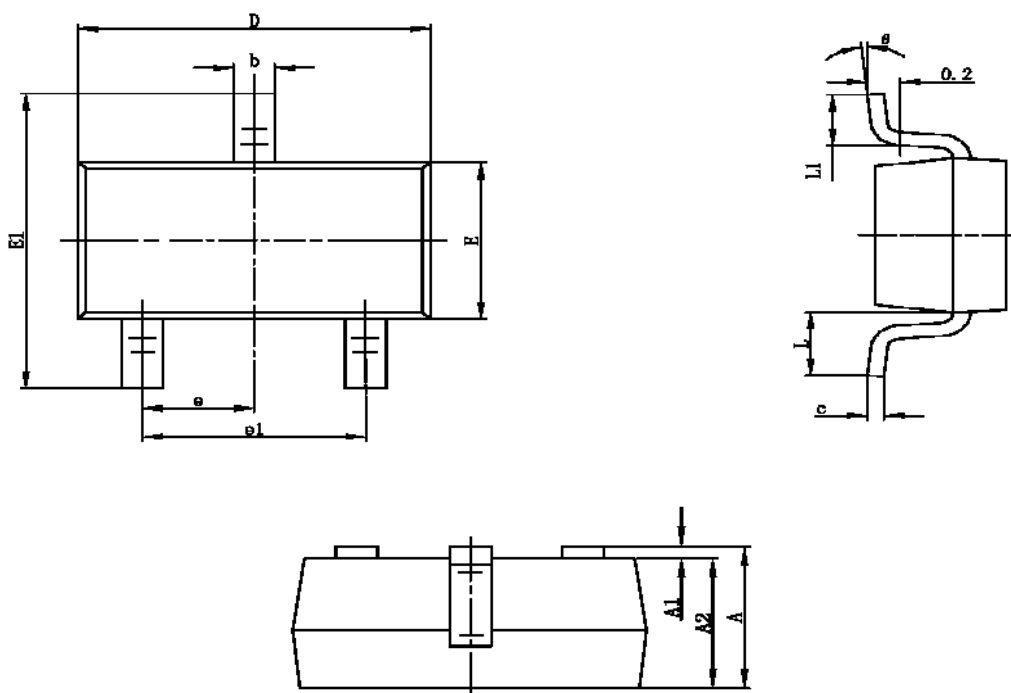
Profile Feature	Pb-Free Assembly Profile
Temperature Min. (T _{Smin})	150°C
Temperature Max. (T _{Smax})	200°C
Time (ts) from (T _{Smin} to T _{Smax})	60-120 seconds
Average Ramp-up Rate (t _L to t _P)	3°C/second max.
Liquidous Temperature (T _L)	217°C
Time (t _L) Maintained Above (T _L)	60 – 150 seconds
Peak Temperature	260°C +0°C / -5°C
Time (t _P) within 5°C of actual Peak Temperature	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.

➤ Ordering Information

Part Number	Description	Quantity
PAN3400SN	SOT-23 Reel	3000 pcs

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➤ Package Information (SOT-23)



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.400	0.012	0.016
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.700REF		0.028REF	
L1	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

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